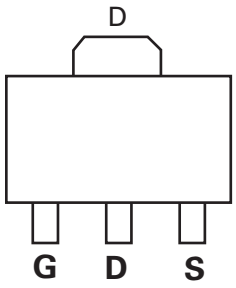
RU20P5E-VB Datasheet
P-Channel 20 V (D-S) MOSFET

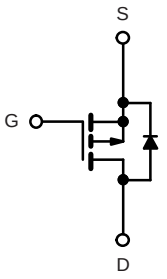
PRODUCT SUMMARY			
V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
- 20	0.055 at V_{GS} = - 4.5 V	- 6[a]	12 nC
	0.060 at V_{GS} = - 3.6 V	- 5.8[a]	
	0.065 at V_{GS} = - 2.5 V	- 5.6[a]	

FEATURES

- **Halogen-free According to IEC 61249-2-21 Definition**
- Trench Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC

Pb-free
RoHS COMPLIANT





P-Channel MOSFET

APPLICATIONS

- Portable Devices
  - Load Switch
  - Charger Switch
  - Battery Switch
  - DC/DC Converter

ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C, unless otherwise noted)				
Parameter		**Symbol**	**Limit**	**Unit**
Drain-Source Voltage		V_{DS}	- 20	V
Gate-Source Voltage		V_{GS}	± 12	
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	- 6[a]	A
	T_C = 70 °C		- 5[a]	
	T_A = 25 °C		- 5[a, b, c]	
	T_A = 70 °C		- 4.2[b, c]	
Pulsed Drain Current		I_{DM}	- 18	
Continuous Source-Drain Diode Current	T_C = 25 °C	I_S	- 4.8	
	T_A = 25 °C		- 1.9[b, c]	
Maximum Power Dissipation	T_C = 25 °C	P_D	6	W
	T_C = 70 °C		3	
	T_A = 25 °C		2.3[b, c]	
	T_A = 70 °C		1.2[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150	°C
Soldering Recommendations (Peak Temperature)			260	

THERMAL RESISTANCE RATINGS					
Parameter		**Symbol**	**Typical**	**Maximum**	**Unit**
Maximum Junction-to-Ambient	t ≤ 5 s	R_{thJA}	45	55	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	18	22	

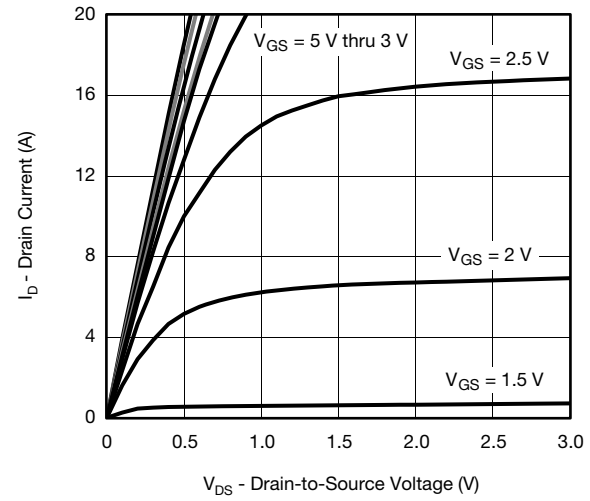
Notes:
a. Package limited.
b. Surface mounted on 1" x 1" FR4 board.
c. t = 5 s.

SPECIFICATIONS (T_J = 25 °C, unless otherwise noted)						
Parameter	**Symbol**	**Test Conditions**	**Min.**	**Typ.**	**Max.**	**Unit**
Static						
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = - 250 µA	- 20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = - 250 µA		- 14		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			3.2		
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = - 250 µA	- 0.5		- 1.4	V
Gate-Source Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 12 V			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = - 20 V, V_{GS} = 0 V			- 1	µA
		V_{DS} = - 20 V, V_{GS} = 0 V, T_J = 85 °C			- 5	
On-State Drain Current[a]	$I_{D(on)}$	$V_{DS} \leq$ - 5 V, V_{GS} = - 4.5 V	- 20			A
Drain-Source On-State Resistance[a]	$R_{DS(on)}$	V_{GS} = - 4.5 V, I_D = - 4.9 A		0.055		Ω
		V_{GS} = - 3.6 V, I_D = - 4.6 A		0.060		
		V_{GS} = - 2.5 V, I_D = - 2.0 A		0.065		
Forward Transconductance[a]	g_{fs}	V_{DS} = - 10 V, I_D = - 4.9 A		16		S
Dynamic[b]						
Input Capacitance	C_{iss}	V_{DS} = - 10 V, V_{GS} = 0 V, f = 1 MHz		1000		pF
Output Capacitance	C_{oss}			225		
Reverse Transfer Capacitance	C_{rss}			195		
Total Gate Charge	Q_g	V_{DS} = - 10 V, V_{GS} = - 10 V, I_D = - 6.5 A		25	38	nC
		V_{DS} = - 10 V, V_{GS} = - 4.5 V, I_D = - 6.5 A		12.5	19	
Gate-Source Charge	Q_{gs}			2		
Gate-Drain Charge	Q_{gd}			4		
Gate Resistance	R_g	f = 1 MHz	0.9	4.6	9.2	Ω
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = 1.9 Ω $I_D \cong$ - 5.2 A, V_{GEN} = - 4.5 V, R_g = 1 Ω		25	50	ns
Rise Time	t_r			20	40	
Turn-Off Delay Time	$t_{d(off)}$			30	60	
Fall Time	t_f			12	25	
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = - 10 V, R_L = - 1.9 Ω $I_D \cong$ - 5.2 A, V_{GEN} = - 10 V, R_g = 1 Ω		10	20	
Rise Time	t_r			10	20	
Turn-Off Delay Time	$t_{d(off)}$			27	55	
Fall Time	t_f			12	25	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C			- 6	A
Pulse Diode Forward Current	I_{SM}				- 20	
Body Diode Voltage	V_{SD}	I_S = - 5.2 A, V_{GS} = 0 V		- 0.8	- 1.2	V
Body Diode Reverse Recovery Time	t_{rr}	I_F = - 5.2 A, dI/dt = 100 A/µs, T_J = 25 °C		20	40	ns
Body Diode Reverse Recovery Charge	Q_{rr}			10	20	nC
Reverse Recovery Fall Time	t_a			10		ns
Reverse Recovery Rise Time	t_b			10		

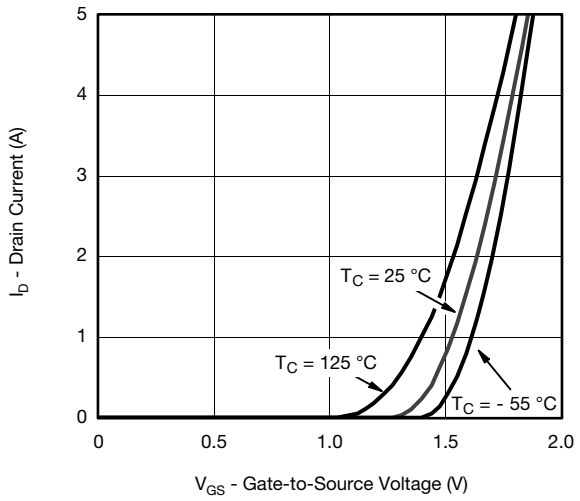
Notes:
a. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.
b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

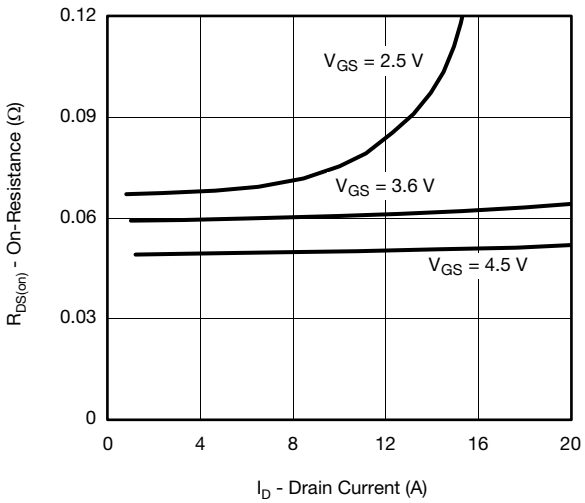
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



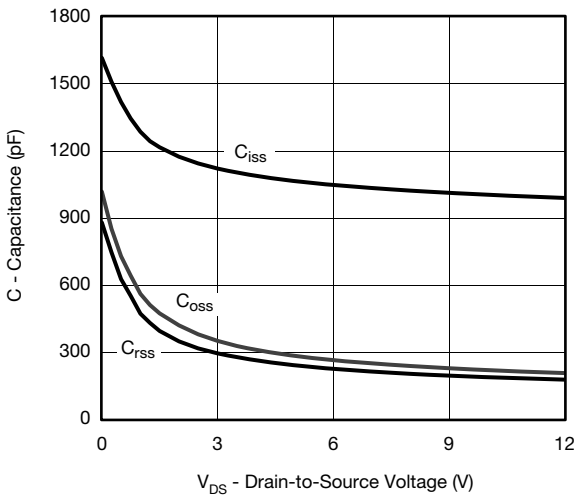
Output Characteristics



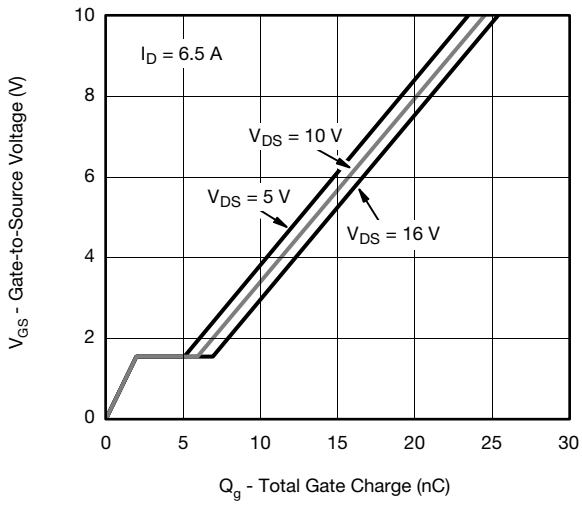
Transfer Characteristics



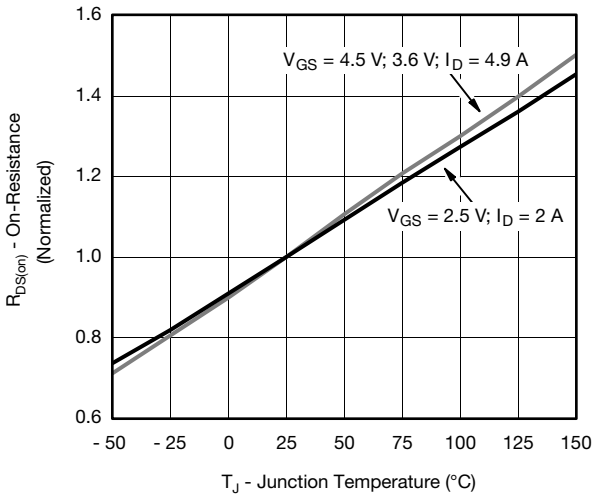
On Resistance vs. Drain Current



Capacitance

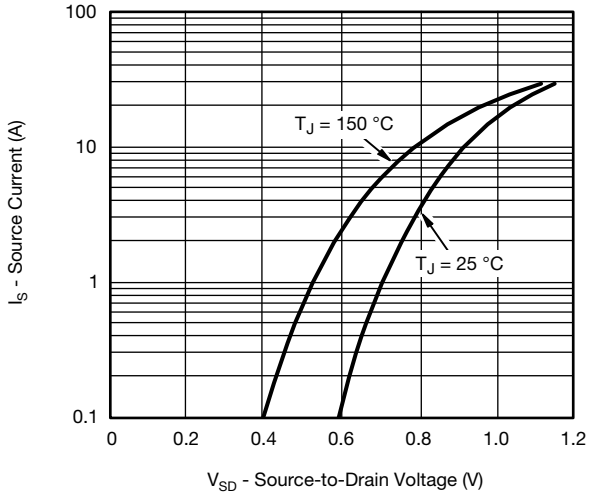


Gate Charge

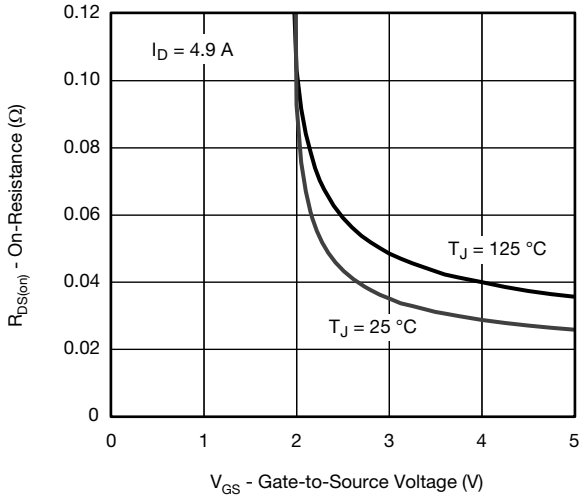


On-Resistance vs. Junction Temperature

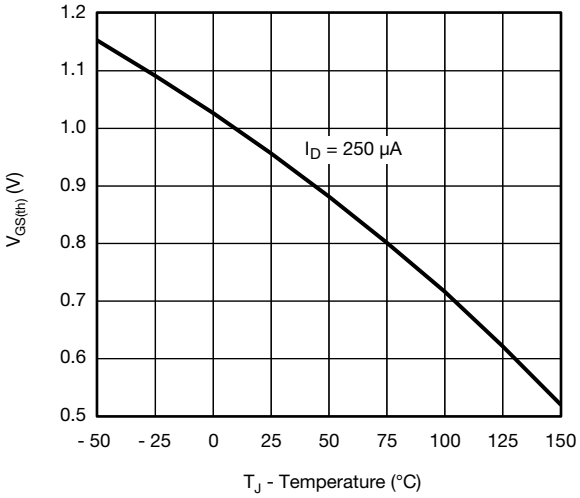
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



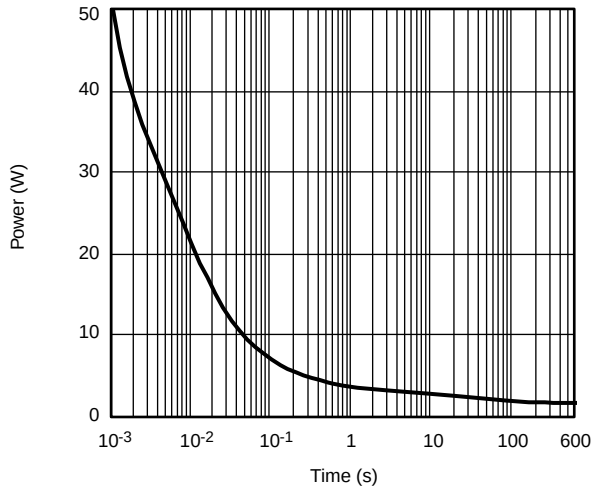
Forward Diode Voltage vs. Temperature



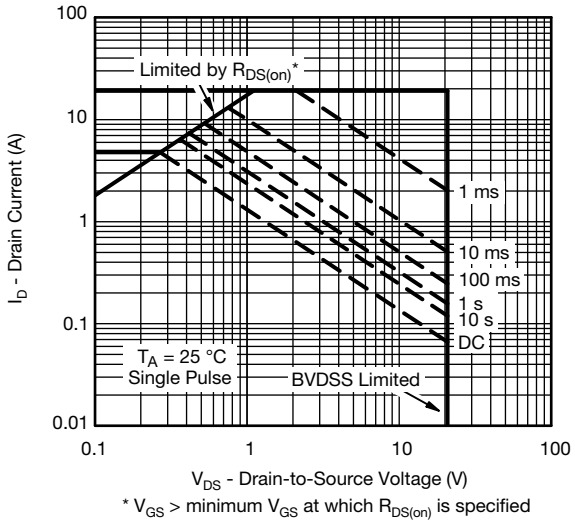
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



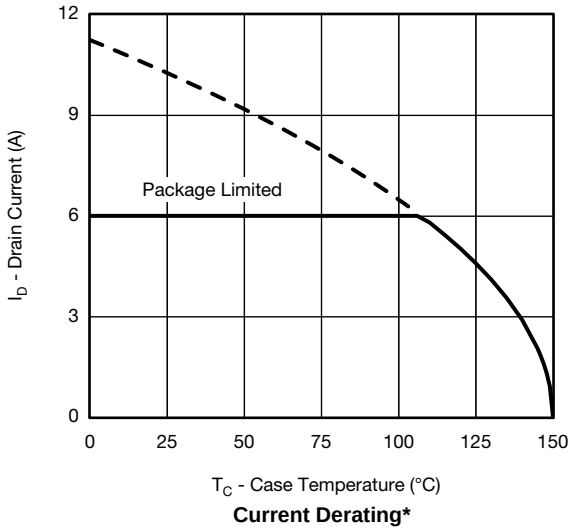
Single Pulse Power



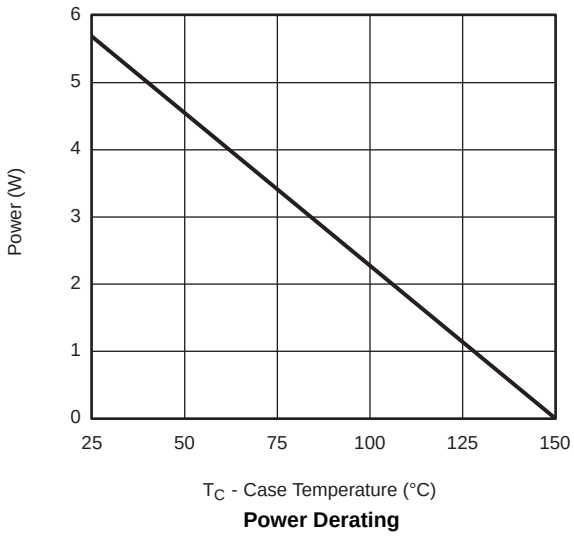
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



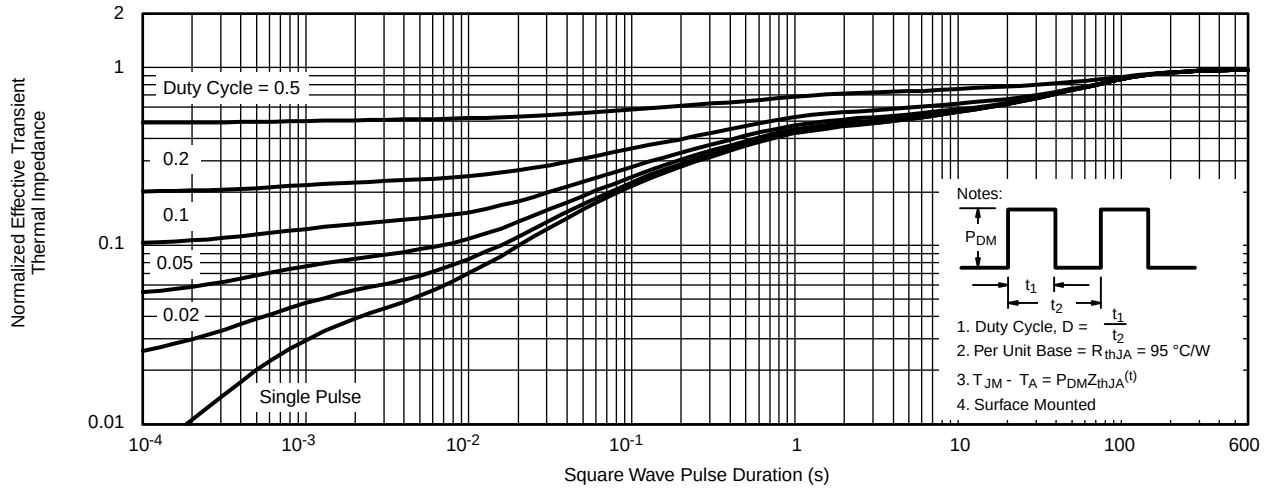
Current Derating*



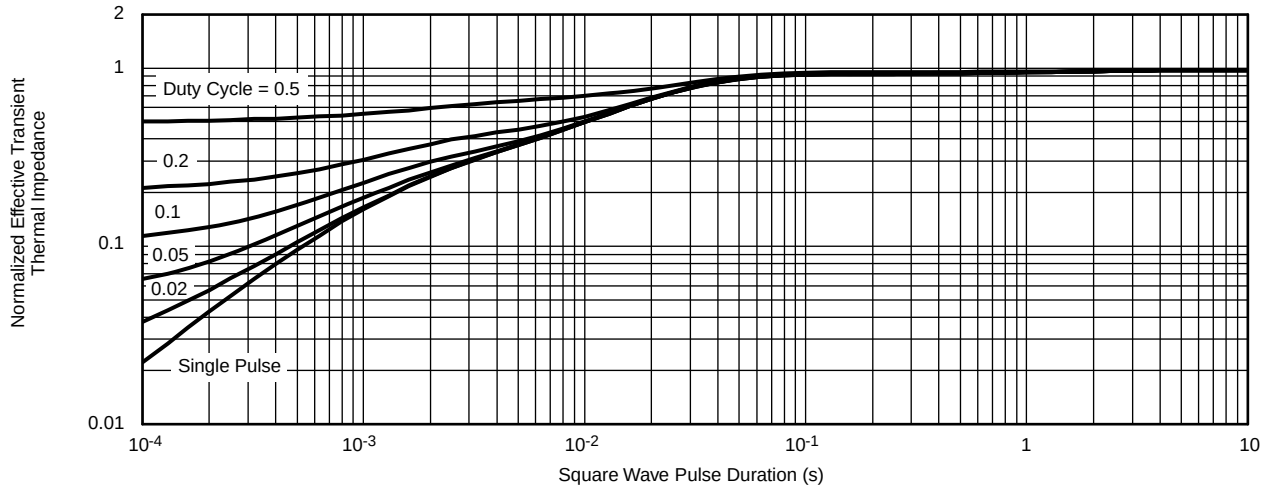
Power Derating

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

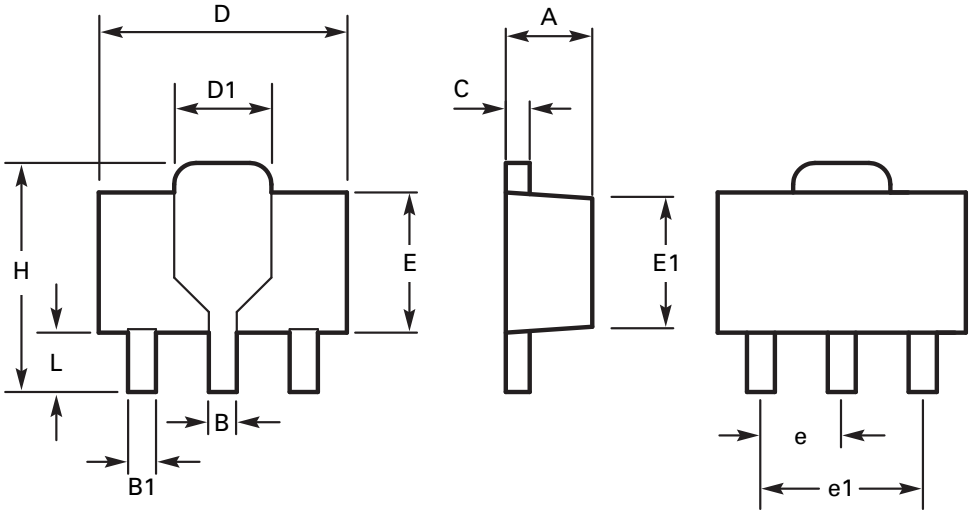


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Package outline - SOT89



DIM	Millimeters		Inches		DIM	Millimeters		Inches	
	Min	Max	Min	Max		Min	Max	Min	Max
A	1.40	1.60	0.550	0.630	E	2.29	2.60	0.090	0.102
B	0.44	0.56	0.017	0.022	E1	2.13	2.29	0.084	0.090
B1	0.36	0.48	0.014	0.019	e	1.50 BSC		0.059 BSC	
C	0.35	0.44	0.014	0.017	e1	3.00 BSC		0.118 BSC	
D	4.40	4.60	0.173	0.181	H	3.94	4.25	0.155	0.167
D1	1.62	1.83	0.064	0.072	L	0.89	1.20	0.035	0.047

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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